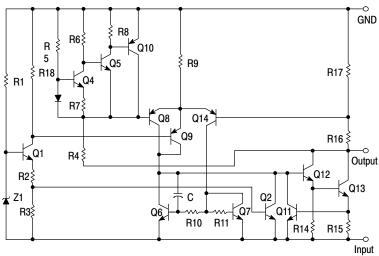
100 mA Negative Voltage Regulators

The MC79L00A Series negative voltage regulators are inexpensive, easy—to—use devices suitable for numerous applications requiring up to 100 mA. Like the higher powered MC7900 Series negative regulators, this series features thermal shutdown and current limiting, making them remarkably rugged. In most applications, no external components are required for operation.

The MC79L00A devices are useful for on-card regulation or any other application where a regulated negative voltage at a modest current level is needed. These regulators offer substantial advantage over the common resistor/Zener diode approach.

Features

- No External Components Required
- Internal Short Circuit Current Limiting
- Internal Thermal Overload Protection
- Low Cost
- Complementary Positive Regulators Offered (MC78L00 Series)
- Pb-Free Packages are Available



* Automotive temperature range selections are available with special test conditions and additional tests in 5, 12 and 15 V devices. Contact your local ON Semiconductor sales office for information.

Figure 1. Representative Schematic Diagram



ON Semiconductor®

www.onsemi.com

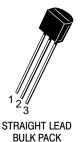
THREE-TERMINAL LOW CURRENT NEGATIVE FIXED VOLTAGE REGULATORS

MARKING DIAGRAMS

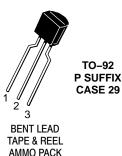


5. GND 6. V_{in} 7. V_{in} 8. NC



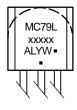


CASE 751



Pin 1. Ground

Input
 Output



xxx = Specific Device Code A = Assembly Location

L = Wafer Lot Y = Year W = Work Week y = B or C

y = B or C = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

MAXIMUM RATINGS ($T_A = +25^{\circ}C$, unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage (-5 V) (-12, -15, -18 V) (-24 V)	V _I	-30 -35 -40	Vdc
Power Dissipation Case 29 (TO–92 Type) T _A = 25°C Thermal Resistance, Junction–to–Ambient Thermal Resistance, Junction–to–Case Case 751 (SOIC–8 Type) (Note 1) T _A = 25°C Thermal Resistance, Junction–to–Ambient Thermal Resistance, Junction–to–Ambient Thermal Resistance, Junction–to–Case	PD R _{θJA} R _{θJC} PD R _{θJA} R _{θJC}	Internally Limited 160 83 Internally Limited 180 45	W °C/W °C/W °C/W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Human Body Model 2000 V per MIL_STD_883, Method 3015

Machine Model Method 200 V.

ELECTRICAL CHARACTERISTICS (V_I = -10 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		М	C79L05AC, A	AΒ	
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	Vo	-4.8	-5.0	-5.2	Vdc
Input Regulation ($T_J = +25^{\circ}C$) $-7.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}$ $-8.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}$	Reg _{line}	- -	- -	150 100	mV
Load Regulation $T_J = +25^{\circ}C, 1.0 \text{ mA} \le I_O \le 100 \text{ mA}$ $1.0 \text{ mA} \le I_O \le 40 \text{ mA}$	Reg _{load}	- -	- -	60 30	mV
Output Voltage $ -7.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}, \ 1.0 \text{ mA} \le I_O \le 40 \text{ mA} $ $V_I = -10 \text{ Vdc}, \ 1.0 \text{ mA} \le I_O \le 70 \text{ mA} $	Vo	-4.75 -4.75	- -	-5.25 -5.25	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.0 5.5	mA
Input Bias Current Change -8.0 $Vdc \ge V_1 \ge -20 \ Vdc$ 1.0 $mA \le I_O \le 40 \ mA$	I _{IB}	- -	- -	1.5 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _n	_	40	_	μV
Ripple Rejection ($-8.0 \ge V_I \ge -18$ Vdc, f = 120 Hz, $T_J = +25^{\circ}C$)		41	49	_	dB
Dropout Voltage ($I_O = 40 \text{ mA}, T_J = +25^{\circ}\text{C}$)	V _I -V _O	_	1.7	_	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{1.} SOIC-8 Junction-to-Ambient Thérmal Resistance is for minimum recommended pad size. Refer to Figure 9 for Thermal Resistance variation versus pad size.

^{*}This device series contains ESD protection and exceeds the following tests:

ELECTRICAL CHARACTERISTICS (V_I = -19 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		MC79L12AC, AB			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	Vo	-11.5	-12	-12.5	Vdc
Input Regulation (T _J = +25°C) $-14.5 \text{ Vdc} \ge V_l \ge -27 \text{ Vdc}$ $-16 \text{ Vdc} \ge V_l \ge -27 \text{ Vdc}$	Reg _{line}		- -	250 200	mV
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \ \text{mA} \le I_O \le 100 \ \text{mA}$ $1.0 \ \text{mA} \le I_O \le 40 \ \text{mA}$	Reg _{load}	- -	- -	100 50	mV
Output Voltage $-14.5 \text{ Vdc} \ge V_l \ge -27 \text{ Vdc}, \ 1.0 \text{ mA} \le I_O \le 40 \text{ mA} \\ V_l = -19 \text{ Vdc}, \ 1.0 \text{ mA} \le I_O \le 70 \text{ mA}$	Vo	-11.4 -11.4	- -	-12.6 -12.6	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.5 6.0	mA
Input Bias Current Change -16 Vdc \geq V _I \geq -27 Vdc 1.0 mA \leq I _O \leq 40 mA	I _{IB}	- -	- -	1.5 0.2	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _n	-	80	_	μV
Ripple Rejection ($-15 \le V_1 \le -25 \text{ Vdc}$, f = 120 Hz, $T_J = +25^{\circ}\text{C}$)	RR	37	42	_	dB
Dropout Voltage (I _O = 40 mA, T _J = +25°C)	V _I -V _O	_	1.7	_	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -23 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		MC79L15AC, AB			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	Vo	-14.4	-15	-15.6	Vdc
Input Regulation ($T_J = +25^{\circ}C$) -17.5 Vdc $\geq V_I \geq -30$ Vdc -20 Vdc $\geq V_I \geq -30$ Vdc	Reg _{line}	_ _ _	- -	300 250	mV
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \ \text{mA} \le I_O \le 100 \ \text{mA}$ $1.0 \ \text{mA} \le I_O \le 40 \ \text{mA}$	Reg _{load}	_ _ _	- -	150 75	mV
Output Voltage $-17.5 \text{ Vdc} \ge V_l \ge -\text{Vdc}, \ 1.0 \text{ mA} \le I_O \le 40 \text{ mA} \\ V_l = -23 \text{ Vdc}, \ 1.0 \text{ mA} \le I_O \le 70 \text{ mA}$	Vo	-14.25 -14.25	_ _	-15.75 -15.75	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	- -	6.5 6.0	mA
Input Bias Current Change -20 Vdc \geq V _I \geq -30 Vdc 1.0 mA \leq I _O \leq 40 mA	Δl_{IB}	_ _ _	- -	1.5 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _N	-	90	-	μV
Ripple Rejection ($-18.5 \le V_I \le -28.5 \text{ Vdc}$, f = 120 Hz)	RR	34	39	-	dB
Dropout Voltage $I_O = 40$ mA, $T_J = +25^{\circ}C$	V _I -V _O	_	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -27 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC), unless otherwise noted).

		MC79L18AC				
Characteristics	Symbol	Min	Тур	Max	Unit	
Output Voltage ($T_J = +25^{\circ}C$)	Vo	-17.3	-18	-18.7	Vdc	
Input Regulation $(T_J = +25^{\circ}C)$ $-20.7 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$ $-21.4 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$ $-22 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$ $-21 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$	Reg _{line}	- - - -	- - - -	325 - - 275	mV	
Load Regulation $T_J = +25^{\circ}\text{C}, \ 1.0 \ \text{mA} \le I_O \le 100 \ \text{mA}$ $1.0 \ \text{mA} \le I_O \le 40 \ \text{mA}$	Reg _{load}	- -		170 85	mV	
Output Voltage $-20.7 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$, $1.0 \text{ mA} \le I_O \le 40 \text{ mA}$ $-21.4 \text{ Vdc} \ge V_I \ge -33 \text{ Vdc}$, $1.0 \text{ mA} \le I_O \le 40 \text{ mA}$ $V_I = -27 \text{ Vdc}$, $1.0 \text{ mA} \le I_O \le 70 \text{ mA}$	Vo	-17.1 - -17.1	- - -	-18.9 - -18.9	Vdc	
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -	_ _	6.5 6.0	mA	
Input Bias Current Change $-21 \text{ Vdc} \ge \text{V}_1 \ge -33 \text{ Vdc}$ $-27 \text{ Vdc} \ge \text{V}_1 \ge -33 \text{ Vdc}$ $1.0 \text{ mA} \le \text{I}_0 \le 40 \text{ mA}$	I _{IB}	- - -	- - -	1.5 _ 0.1	mA	
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _n	-	150	_	μV	
Ripple Rejection ($-23 \le V_1 \le -33 \text{ Vdc}$, f = 120 Hz, T _J = +25°C)		33	48	_	dB	
Dropout Voltage I _O = 40 mA, T _J = +25°C	V _I -V _O	_	1.7	_	Vdc	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -33 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC), unless otherwise noted).

			MC79L24AC		
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage (T _J = +25°C)	Vo	-23	-24	-25	Vdc
Input Regulation ($T_J = +25^{\circ}C$) $-27 \text{ Vdc} \ge V_I \ge -38 \text{ Vdc}$ $-27.5 \text{ Vdc} \ge V_I \ge -38 \text{ Vdc}$ $-28 \text{ Vdc} \ge V_I \ge -38 \text{ Vdc}$	Reg _{line}	- - -	- - -	350 - 300	mV
Load Regulation $T_J = +25^{\circ}\text{C}, \ 1.0 \ \text{mA} \leq I_O \leq 100 \ \text{mA} \\ 1.0 \ \text{mA} \leq I_O \leq 40 \ \text{mA}$	Reg _{load}	- -	- -	200 100	mV
Output Voltage $-27 \text{ Vdc} \geq V_l \geq -38 \text{ V, } 1.0 \text{ mA} \leq I_O \leq 40 \text{ mA} \\ -28 \text{ Vdc} \geq V_l \geq -38 \text{ Vdc, } 1.0 \text{ mA} \leq I_O \leq 40 \text{ mA} \\ V_l = -33 \text{ Vdc, } 1.0 \text{ mA} \leq I_O \leq 70 \text{ mA} \\ \end{cases}$	Vo	-22.8 - -22.8	- - -	-25.2 - -25.2	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}		- -	6.5 6.0	mA
Input Bias Current Change $-28 \text{ Vdc} \ge \text{V}_1 \ge -38 \text{ Vdc}$ $1.0 \text{ mA} \le \text{I}_0 \le 40 \text{ mA}$	$\Delta I_{ m IB}$	- -	- -	1.5 0.1	mA
Output Noise Voltage ($T_A = +25^{\circ}C$, 10 Hz \leq f \leq 100 kHz)	V _n	_	200	-	μV
Ripple Rejection ($-29 \le V_1 \le -35 \text{ Vdc}$, f = 120 Hz, $T_J = +25^{\circ}\text{C}$)		31	47	-	dB
Dropout Voltage I _O = 40 mA, T _J = +25°C	V _I -V _O	_	1.7	_	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

APPLICATIONS INFORMATION

Design Considerations

The MC79L00A Series of fixed voltage regulators are designed with Thermal Overload Protections that shuts down the circuit when subjected to an excessive power overload condition, Internal Short Circuit Protection that limits the maximum current the circuit will pass.

In many low current applications, compensation capacitors are not required. However, it is recommended that the regulator input be bypassed with a capacitor if the regulator is connected to the power supply filter with long wire length, or if the output load capacitance is large. An input bypass capacitor should be selected to provide good

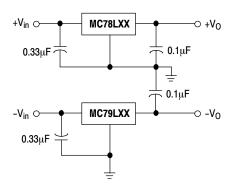
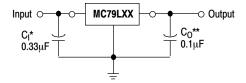


Figure 2. Positive and Negative Regulator

high–frequency characteristics to insure stable operation under all load conditions. A 0.33 μF or larger tantalum, mylar, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with the shortest possible leads directly across the regulator's input terminals. Normally good construction techniques should be used to minimize ground loops and lead resistance drops since the regulator has no external sense lead. Bypassing the output is also recommended.



A common ground is required between the input and the output voltages. The input voltage must remain typically 2.0 V above the output voltage even during the low point on the ripple voltage.

- * C_I is required if regulator is located an appreciable distance from the power supply filter
- ** Co improves stability and transient response.

Figure 3. Standard Application

TYPICAL CHARACTERISTICS

 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

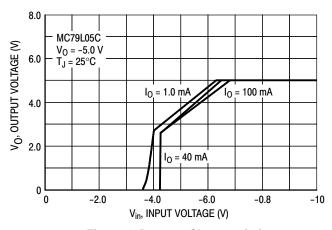


Figure 4. Dropout Characteristics

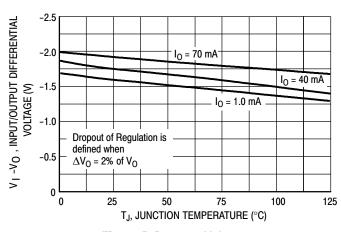


Figure 5. Dropout Voltage versus Junction Temperature

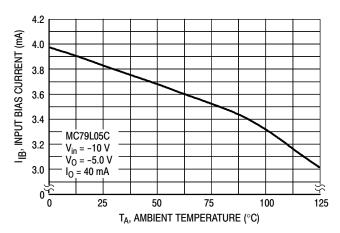


Figure 6. Input Bias Current versus Ambient Temperature

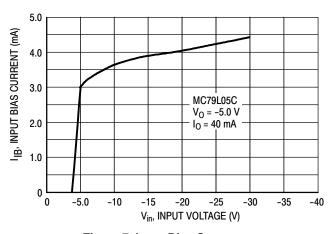


Figure 7. Input Bias Current versus Input Voltage

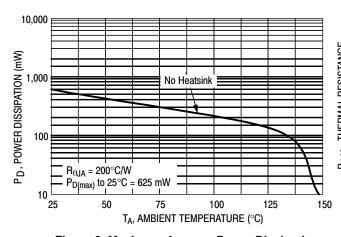


Figure 8. Maximum Average Power Dissipation versus Ambient Temperature (TO-92)

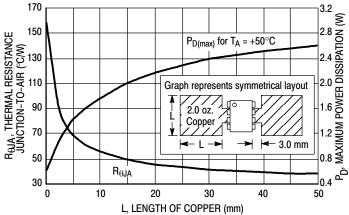


Figure 9. SOP-8 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

ORDERING INFORMATION

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping [†]
MC79L05ABDG	-5.0 V	TJ = −40° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L05ABPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L05ACDG		TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L05ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L05ACPRMG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L05ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L12ABDG	-12 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L12ABPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L12ACDG	–12 V	TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L12ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L12ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box

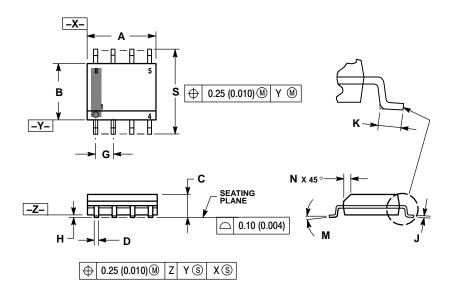
ORDERING INFORMATION (continued)

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping [†]
MC79L15ABDG	–15 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}C$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ABDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ABPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L15ABPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L15ACDG		TJ = 0° to +125°C	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ACPG			TO-92 (Pb-Free)	2000 Units / Bag
MC79L15ACPRAG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L15ACPREG			TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L15ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L18ABPRPG	–18 V	TJ = -40° to +125°C	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L18ACPG		TJ = 0° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ABPG	-24 V	TJ = -40° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ACPG		TJ = 0° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ACPRMG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L24ACPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 **ISSUE AK**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

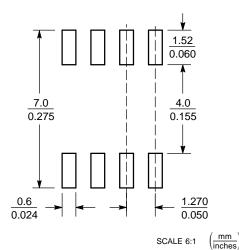
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE

- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
 PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 6. 751–01 THRU 751–06 ARE OBSOLETE. NEW
 STANDARD IS 751.07
- STANDARD IS 751-07.

	MILLIN	MILLIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.05	0 BSC
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

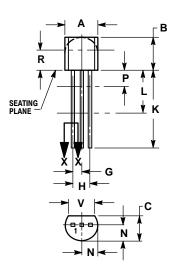
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



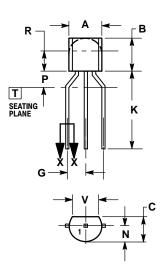
STRAIGHT LEAD **BULK PACK**



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
v	0.135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION:
- MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED.

 LEAD DIMENSION IS UNCONTROLLED IN

 P AND BEYOND DIMENSION K MINIMUM.

FAN	MILLIMETERS			
DIM	MIN	MAX		
Α	4.45	5.20		
В	4.32	5.33		
С	3.18	4.19		
D	0.40	0.54		
G	2.40	2.80		
J	0.39	0.50		
K	12.70			
N	2.04	2.66		
P	1.50	4.00		
R	2.93			
٧	3.43			

ON Semiconductor and 📖 are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor and [11] are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.nsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications union provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and h expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your loca Sales Representative